MJE13003D

Preliminary

NPN SILICON TRANSISTOR

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

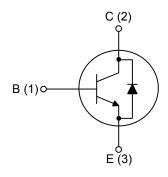
■ DESCRIPTION

The UTC **MJE13003D** is a NPN Power Transistor. It is intended to be used in applications requiring medium voltage capability and high switching speeds.

■ FEATURES

- * Fast-Switching And High Voltage Capability
- * Dynamic Parameters With Low Spread
- * High Reliability
- * Integrated Antiparallel Collector-Emitter Diode

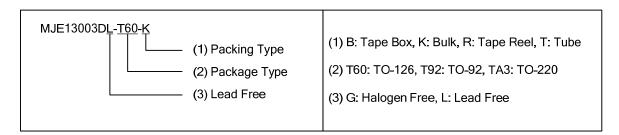
■ INTERNAL SCHEMATIC DIAGRAM



TO-92 TO-126 TO-220

ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MJE13003DL-T60-K	MJE13003DG-T60-K	TO-126	В	С	Е	Bulk	
MJE13003DL-T92-B	MJE13003DG-T92-B	TO-92	В	С	Е	Tape Box	
MJE13003DL-T92-K	MJE13003DG-T92-K	TO-92	В	С	Е	Bulk	
MJE13003DL-T92-R	MJE13003DG-T92-R	TO-92	В	С	Е	Tape Reel	
MJE13003DL-TA3-T	MJE13003DG-TA3-T	TO-220	В	С	Е	Tube	



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector- Emitter Voltage (V _{BE} =	ollector- Emitter Voltage (V _{BE} =0)		700	V	
Collector-Emitter Voltage (I _B =0)		V_{CEO}	400	V	
Emitter-Base Voltage (I _C =0, I _B =0.75A, t _P <10µS)		V_{EBO}	9	V	
Collector Current		I _C	1.5	Α	
Collector Peak Current (t _P <5ms)		I _{CM}	3	Α	
Base Current		I _B	0.75	Α	
Base Peak Current (t _P <5ms)		I _{BM}	1.5	Α	
	TO-126		40	W	
Power Dissipation (T _C =25°C)	TO-92	P _D	30		
	TO-220		70		
Junction Temperature		TJ	150	°C	
Storage Temperature		T _{STG}	-55 ~ + 150	Ŝ	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

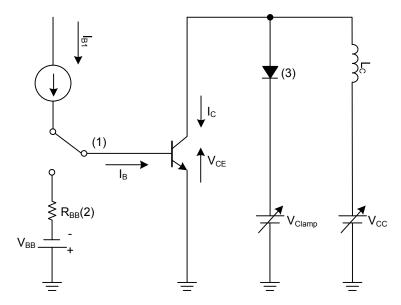
■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Emitter-Base Breakdown Voltage		BV_{EBO}	I _E =10mA, I _C =0	9		18	V
Collector-Emitter Sustaining Voltage (Note)		$V_{CEO(SUS)}$	I _C =10mA, I _B =0	400			V
Collector Cut-Off Current		I _{CES}	V _{CE} =700V,V _{BE} =0			1	mA
Collector-Emitter Saturation Voltage (Note)		V _{CE(SAT)}	I _C =0.5 A, I _B =0.1 A			0.5	V
			I _C =1 A, I _B =0.25 A			1	V
			I _C =1.5 A, I _B =0.5 A			3	V
Base-Emitter Saturation Voltage (Note)		V _{BE(SAT)}	I _C =0.5 A, I _B =0.1 A			1	V
			I _C =1 A, I _B =0.25 A			1.2	V
DC Current Gain		h _{FE}	I _C =0.5A, V _{CE} =5 V	8		51	
			I _C =1 A, V _{CE} =5 V	5		30	
	Rise Time	t_R	V _{CC} =125 V, I _C =1 A,			1	μs
Resistive Load	Storage Time	ts	I _{B1} =0.2 A, I _{B2} =-0.2 A			4	μs
	Fall Time	t_{F}	t _P =25µs			0.7	μs
Inductive Load Storage Time		ts	I _C =1 A, I _{B1} =0.2 A,V _{BE} =-5 V,		0.8		
			L=50mH, V _{CLAMP} =300V				μs
Diode Forward Voltage		V_{F}	I _F =0.5 A			1.5	V

Note: Pulse Test: Pulse duration≤300µs, Duty cycle≤2 %

■ TEST CIRCURTS

Inductive Load Switching Test Circuit

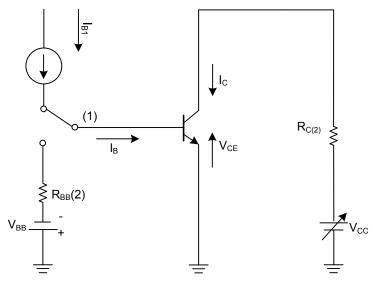


Notes: 1. Fast Electronic Switch

2. Non-Inductive Resistor

3. Fast Recovery Rectifier

Resistive Load Switching Test Circuit



Notes: 1. Fast Electronic Switch

2. Non-Inductive Resistor

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